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# 10

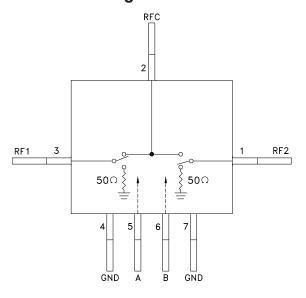
# GaAs MMIC SMT HIGH ISOLATION SPDT SWITCH, DC - 6 GHz

## Typical Applications

The HMC232G7 is ideal for:

- Telecom Infrastructure
- Microwave Radio & VSAT
- Military Radios, Radar & ECM
- Space Systems
- Test Instrumentation

# **Functional Diagram**



#### **Features**

Isolation: 55 dB @ 2 GHz

42 dB @ 6 GHz

Insertion Loss: 1.9 dB Typical @ 6 GHz

Non-Reflective Design

Hermetic Surface Mount Package
Direct Replacement for HMC132G7

## **General Description**

The HMC232G7 is a broadband high isolation non-reflective GaAs MESFET SPDT switch in a hermetic surface mount package. Covering DC to 6 GHz, the switch features >55 dB isolation up to 2 GHz and >42 dB isolation up to 6 GHz. The switch operates using complementary negative control voltage logic lines of -5/0V and requires no bias supply. This product is a form, fit & functional replacement for the HMC132G7.

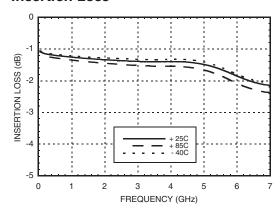
# Electrical Specifications, $T_A = +25^{\circ}$ C, With 0/-5V Control, 50 Ohm System

Parameter	Frequency	Min.	Тур.	Max.	Units
Insertion Loss	DC - 2.0 GHz DC - 4.0 GHz DC - 6.0 GHz		1.3 1.4 1.9	1.6 1.7 2.3	dB dB dB
Isolation	DC - 2.0 GHz DC - 4.0 GHz DC - 6.0 GHz	50 41 37	55 46 42		dB dB dB
Return Loss "On State	DC - 2.0 GHz DC - 4.0 GHz DC - 6.0 GHz		18 17 12		dB dB dB
Return Loss RF1, RF2 "Off State	DC - 2.0 GHz DC - 4.0 GHz DC - 6.0 GHz		14 13 11		dB dB dB
Input Power for 1 dB Compression	0.5 - 6.0 GHz	23	27		dBm
Input Third Order Intercept (Two-Tone Input Power= +7 dBm Each Tone, 1 MHz Tone Separation	0.5 - 6.0 GHz		49		dBm
Switching Characteristics tRISE, tFALL (10/90% RF) tON, tOFF (50% CTL to 10/90% RF)	DC - 6.0 GHz		3 6		ns ns

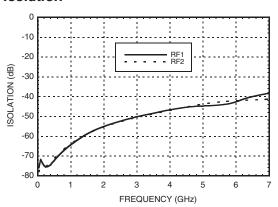


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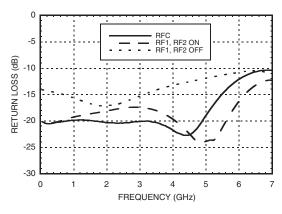
#### Insertion Loss



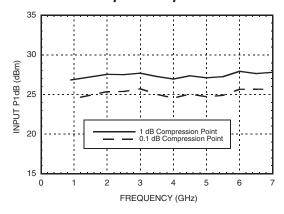
#### Isolation



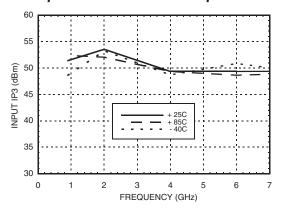
#### **Return Loss**



#### 0.1 and 1 dB Input Compression Point



## **Input Third Order Intercept Point**



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## **Absolute Maximum Ratings**

RF Input Power (V <sub>A</sub> , V <sub>B</sub> = 0/-5V) (0.5 - 6 GHz)	+30 dBm (@ +50 °C)
Control Voltage Range (A & B)	+1.0V to -7.5 Vdc
Channel Temperature	150 °C
Thermal Resistance (R <sub>TH</sub> ) (junction to lead)	94 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C
ESD Sensitivity (HBM)	Class 1A



## **Control Voltages**

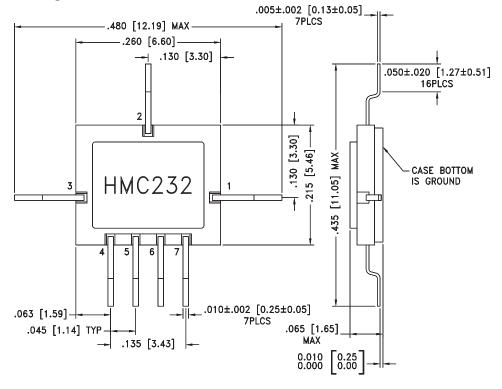
State	Bias Condition
Low	0 to -0.2V @ 10 uA Max.
High	-5V @ 10 uA Typ. to -7V @ 45 uA Typ.

## Truth Table

Control Input		Signal Path State		
Α	В	RFC to RF1	RFC to RF2	
High	Low	ON	OFF	
Low	High	OFF	ON	

Caution: Do not "Hot Switch" power levels greater than +27 dBm ( $V_a$ ,  $V_n$  = 0/-5V).

## **Outline Drawing**



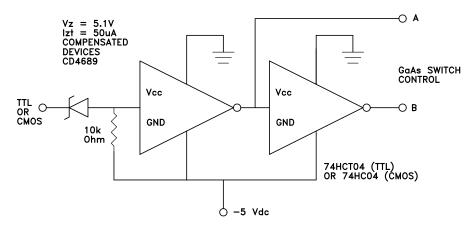
#### NOTES:

- PACKAGE BODY MATERIAL: WHITE ALUMINA 92%
- 2. CONDUCTOR TRACES MATERIAL: THICK FILM TUNGSTEN.
- 3. LEAD, BASE, COVER MATERIAL: KOVAR™.
- 4. PLATING: ELECTROLYTIC GOLD 50 MICROINCHES MIN, OVER ELECTROLYTIC NICKEL 50 MICROINCHES MIN.
- 5. ALL DIMENSIONS ARE IN INCHES [MILLIMETERS].
- 6. TOLERANCES: .±005 [0.13] UNLESS OTHERWISE SPECIFIED.
- 7. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND.



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## **Suggested Driver Circuit**



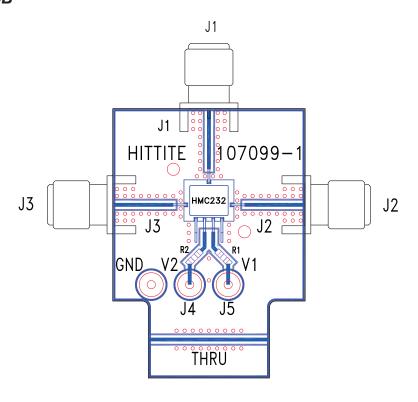
## **Pin Descriptions**

Pin Number	Function	Description	Interface Schematic
1, 2, 3	RF2, RFC, RF1	This pin is DC coupled and matched to 50 Ohm. Blocking capacitors are required if RF line potential is not equal to 0V.	
4, 7	GND	Package bottom must also be connected to PCB RF ground.	○ GND =
5	А	See truth table and control voltage table.	0—
6	В	See truth table and control voltage table.	c



# GaAs MMIC SMT HIGH ISOLATION SPDT SWITCH, DC - 6 GHz

#### **Evaluation PCB**



## List of Materials for Evaluation PBC 107181 [1]

Item	Description
J1 - J3	PCB Mount SMA RF Connector
J4 - J6	DC Pin
R1, R2	100 Ohm Resistor, 0603 Pkg.
U1	HMC232G7 SPDT Switch
PCB [2]	107099 Evaluation PCB

<sup>[1]</sup> Reference this number when ordering complete evaluation PCB

The circuit board used in the final application should be generated with proper RF circuit design techniques. Signal lines at the RF port should have 50 ohm impedance and the package ground leads and package bottom should be connected directly to the ground plane similar to that shown above. The evaluation circuit board shown above is available from Hittite Microwave Corporation upon request.

<sup>[2]</sup> Circuit Board Material: Rogers 4350



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**SWITCHES - SMT** 

GaAs MMIC SMT HIGH ISOLATION SPDT SWITCH, DC - 6 GHz

Notes: